

Low V_F Silicon Power Schottky Diode

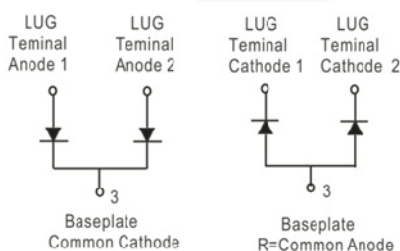
$$V_{RRM} = 20 \text{ V}$$

$$I_{F(AV)} = 600 \text{ A}$$

Features

- High Surge Capability
- Type 20 V V_{RRM}
- Not ESD Sensitive

Twin Tower Package



Maximum ratings, at $T_j = 25^\circ\text{C}$, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	MBR60020CT(R)L	Unit
Maximum recurrent peak reverse voltage	V_{RRM}		20	V
Maximum RMS voltage	V_{RMS}		14	V
Maximum DC blocking voltage	V_{DC}		20	V
Operating temperature	T_j		-55 to 150	$^\circ\text{C}$
Storage temperature	T_{stg}		-55 to 150	$^\circ\text{C}$

Electrical characteristics, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	MBR60020CT(R)L	Unit
Average forward current (per pkg)	$I_{F(AV)}$	$T_C = 100^\circ\text{C}$	600	A
Peak forward surge current (per leg)	I_{FSM}	$t_p = 8.3 \text{ ms}$, half sine	4000	A
Maximum instantaneous forward voltage (per leg)	V_F	$I_{FM} = 300 \text{ A}$, $T_j = 25^\circ\text{C}$	0.58	V
Maximum instantaneous reverse current at rated DC blocking voltage (per leg)	I_R	$T_j = 25^\circ\text{C}$	3	mA
		$T_j = 100^\circ\text{C}$	250	

Thermal characteristics

Maximum thermal resistance, junction - case (per leg)	$R_{\theta JC}$	0.28	$^\circ\text{C/W}$
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Figure .1-Typical Forward Characteristics

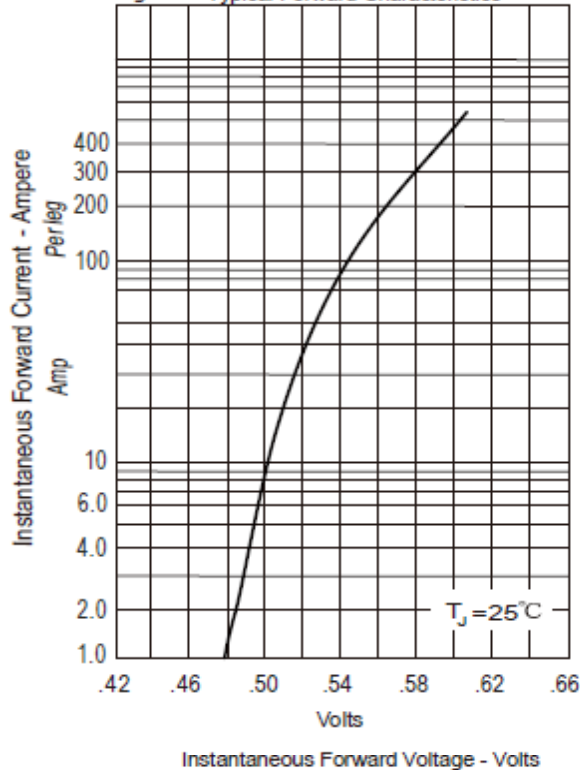


Figure .2- Forward Derating Curve

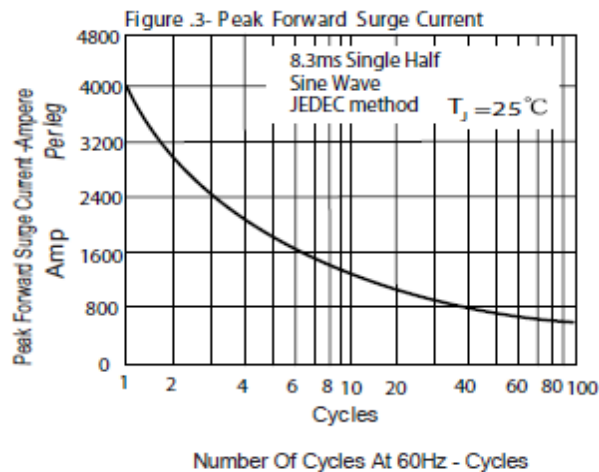
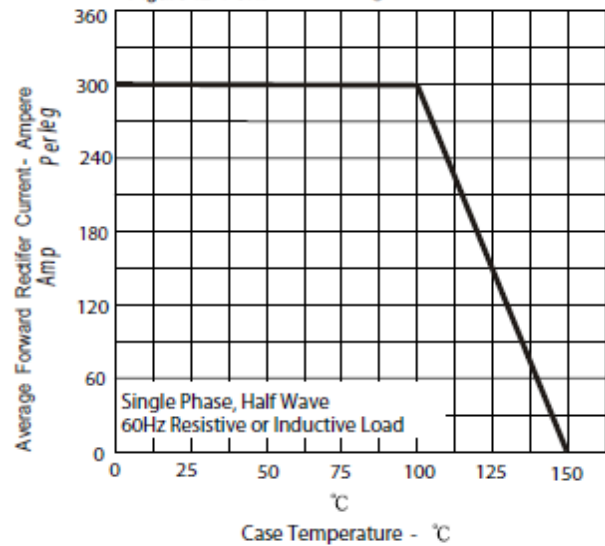
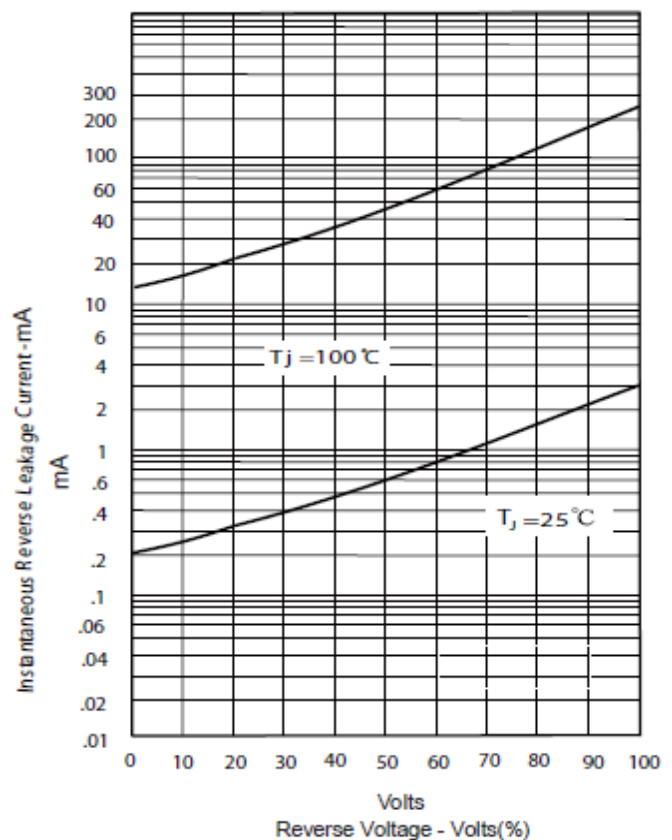
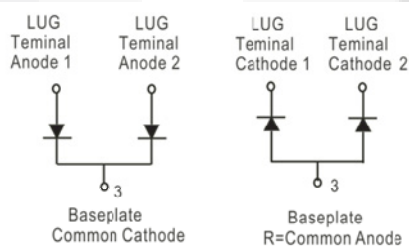
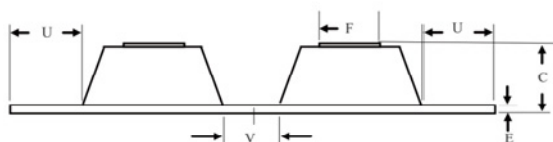
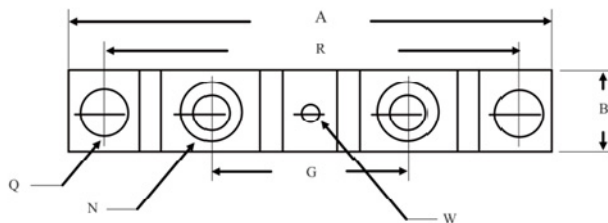


Figure .4- Typical Reverse Characteristics



Package dimensions and terminal configuration

Product is marked with part number and terminal configuration.



DIM	Inches		Millimeters	
	Min	Max	Min	Max
A	-----	3.630	-----	92.40
B	0.700	0.800	17.78	20.32
C	-----	0.650	-----	16.51
E	0.130	0.141	3.30	3.60
F	0.482	0.490	12.25	12.45
G	1.368	BSC	34.75	BSC
N	1/4-20 UNC FULL			
Q	0.275	0.290	6.99	7.37
R	3.150	BSC	80.01	BSC
U	0.600	-----	15.24	-----
V	0.312	0.370	7.92	9.40
W	0.180	0.195	4.57	4.95